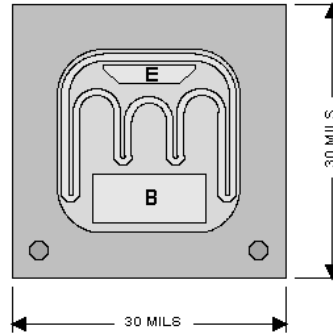


**Chip Type 2C3019**  
**Geometry 4500**  
**Polarity PNP**

**Generic Packaged Parts:**  
**2N3019, 2N3057**



[Request Quotation](#)

Chip type **2C3019** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**

[2N3019](#), [2N3019S](#), [2N3019UB](#), [2N3057](#), [2N3057A](#),  
[2N3700](#), [2N3700UB](#), [SD3019F](#), [SQ3019](#), [SQ3019F](#)

**Product Summary:**

**APPLICATIONS:** Designed for general purpose switching and amplifier applications.

**Features:** [Radiation graphs available](#)

Mechanical Specifications		
Metallization	Top	Al - 12 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	2.3 mils x 7.0 mils
	Base	5.0 mils x 11.0 mils
Die Thickness	8 mils nominal	
Chip Area	30 mils x 30 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
$T_A = 25^\circ\text{C}$				
Parameter	Test conditions	Min	Max	Unit
$BV_{CBO}$	$I_C = 100 \mu\text{A}$ , $I_E = 0$	140	---	V dc
$BV_{EBO}$	$I_E = 100 \mu\text{A}$ , $I_C = 0$	7.0	---	V dc
$I_{CBO}$	$V_{CB} = 40 \text{ V}$ , $I_E = 0$	---	10	nA
$h_{FE}$	$I_C = 150 \text{ mA dc}$ , $V_{CE} = 10 \text{ V}$	100	300	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*